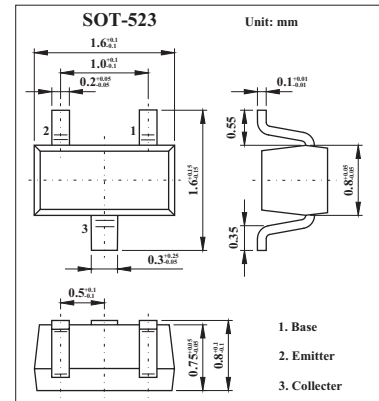


## Silicon PNP Epitaxial Type Transistor 2SA1832

### ■ Features

- High Voltage and High Current :  $V_{CE0} = -50V, I_C = -150mA$  (Max.)
- Excellent  $h_{FE}$  Linearity :  
 $h_{FE}(I_C = -0.1mA) / h_{FE}(I_C = -2mA) = 0.95$  (Typ.)
- High  $h_{FE}$ :  $h_{FE} = 70$  to  $400$



### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-150	mA
Base current	$I_B$	-30	mA
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	125	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ C$

### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -5V, I_E = 0$			-0.1	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current Gain	$h_{FE}$	$V_{CE} = -6V, I_C = -2mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-0.1	-0.3	V
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		4	7	pF
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -1mA$	80			MHz

### ■ $h_{FE}$ Classification

Marking	SQ	SY	SG
Rank	Q	Y	GR
$h_{FE}$	70~140	120~240	200~400